Karen L Kavanagh

List of Publications by Year in Descending Order

192 papers	6,751 citations	38 h-index	79 g-index
205 ext. papers	7,210 ext. citations	4.1 avg, IF	5.44 L-index

#	Paper	IF	Citations
192	Rotational epitaxy of h-BN on Cu (110). *Surface Science*, **2022**, 721, 122080	1.8	1
191	Three-Dimensional Conductive Fingerprint Phantoms Made of Ethylene-Vinyl Acetate/Graphene Nanocomposite for Evaluating Smartphone Scanners. *ACS Applied Electronic Materials*, **2021**, 3, 2097-2105	4	2
190	Geometric effects on carrier collection in core-shell nanowire pn junctions. *Nano Futures*, **2021**, 5, 025007	3.6	
189	Abrupt degenerately-doped silicon nanowire tunnel junctions. *Nanotechnology*, **2020**, 31, 415708	3.4	1
188	Three-Dimensional Imaging of Beam-Induced Biasing of InP/GaInP Tunnel Diodes. *Nano Letters*, **2019**, 19, 3490-3497	11.5	3
187	Understanding gaas Native Oxides By Correlating Three Liquid Contact Angle Analysis (3LCAA) and High Resolution Ion Beam Analysis (HR-IBA) to X-Ray Photoelectron Spectroscopy (XPS) as Function of Surface Processing. *MRS Advances*, **2019**, 4, 2249-2263	0.7	0
186	Axial EBIC oscillations at core/shell GaAs/Fe nanowire contacts. *Nanotechnology*, **2019**, 30, 025701	3.4	2
185	Role of Hydrogen Evolution during Epitaxial Electrodeposition of Fe on GaAs. *Journal of the Electrochemical Society*, **2018**, 165, H3076-H3079	3.9	8
184	Growth of h-BN on copper (110) in a LEEM. *Surface Science*, **2018**, 669, 133-139	1.8	8
183	Measuring Surface Energies of GaAs (100) and Si (100) by Three Liquid Contact Angle Analysis (3LCAA) for Heterogeneous Nano-BondingTM. *MRS Advances*, **2018**, 3, 3403-3411	0.7	3
182	Electrical characterization of Si/InN nanowire heterojunctions. *Semiconductor Science and Technology*, **2018**, 33, 015008	1.8	3
181	Aligned cuboid iron nanoparticles by epitaxial electrodeposition. *Nanoscale*, **2017**, 9, 5315-5322	7.7	6
180	Space-charge-limited current in nanowires. *Journal of Applied Physics*, **2017**, 121, 174301	2.5	15
179	Electrical properties of lightly Ga-doped ZnO nanowires. *Semiconductor Science and Technology*, **2017**, 32, 125010	1.8	6
178	Regrowth mechanism for oxide isolation of GaAs nanowires. *Nanotechnology*, **2017**, 28, 385302	3.4	3
177	Interfacial reactions at Fe/topological insulator spin contacts. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2017**, 35, 04F105	1.3	6
176	Magnetic phase shift reconstruction for uniformly magnetized nanowires. *Ultramicroscopy*, **2017**, 172, 10-16	3.1	

175	Direct Measurement of the Electrical Abruptness of a Nanowire p-n Junction. *Nano Letters*, **2016**, 16, 3982-8	11.5	18
174	Lithography-Free Fabrication of Core-Shell GaAs Nanowire Tunnel Diodes. *Nano Letters*, **2015**, 15, 5408-13	11.5	14
173	Recycling gold nanohole arrays. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2014**, 32, 031403	2.9	5
172	Characterization of solution-bonded GaAs/InGaAs/GaAs features on GaAs. *Semiconductor Science and Technology*, **2014**, 29, 075009	1.8	2
171	Magnetic Characterization of Isolated CoFeB/Cu Nanowires by Off-Axis Electron Holography. *Microscopy and Microanalysis*, **2014**, 20, 280-281	0.5	
170	Hanle measurements of electrodeposited Fe/GaAs spin tunnel contacts. *Journal of Applied Physics*, **2014**, 115, 123709	2.5	2
169	Large-Area Low-Cost Flexible Plastic Nanohole Arrays for Integrated Bio-Chemical Sensing. *IEEE Sensors Journal*, **2013**, 13, 3982-3990	4	13
168	Improved chemical and electrical stability of gold silicon contacts via epitaxial electrodeposition. *Journal of Applied Physics*, **2013**, 113, 063708	2.5	5
167	Direct measurement of coherency limits for strain relaxation in heteroepitaxial core/shell nanowires. *Nano Letters*, **2013**, 13, 1869-76	11.5	69
166	Lateral spin injection and detection through electrodeposited Fe/GaAs contacts. *Semiconductor Science and Technology*, **2013**, 28, 035003	1.8	7
165	Growth and strain relaxation of GaAs and GaP nanowires with GaSb shells. *Journal of Applied Physics*, **2013**, 113, 134309	2.5	20
164	Probing the electrical transport properties of intrinsic InN nanowires. *Applied Physics Letters*, **2013**, 102, 073102	3.4	44
163	Geometric limits of coherent III-V core/shell nanowires. *Journal of Applied Physics*, **2013**, 114, 054301	2.5	34
162	Reduction of Gold Penetration through Phenyl-Terminated Alkyl Monolayers on Silicon. *Journal of Physical Chemistry C*, **2012**, 116, 17040-17047	3.8	23
161	Epitaxial Growth of Metals on Semiconductors Via Electrodeposition **2012**, 217-235		1
160	Faster radial strain relaxation in InAs□GaAs core□shell heterowires. *Journal of Applied Physics*, **2012**, 111, 044301	2.5	48
159	Metastable phase formation in the Au-Si system via ultrafast nanocalorimetry. *Journal of Applied Physics*, **2012**, 111, 093516	2.5	20
158	p-type doping of GaAs nanowires using carbon. *Journal of Applied Physics*, **2012**, 112, 094323	2.5	14

157	Controlled axial and radial Te-doping of GaAs nanowires. *Journal of Applied Physics*, **2012**, 112, 054324	2.5	11
156	Insights into semiconductor nanowire conductivity using electrodeposition. *Semiconductor Science and Technology*, **2012**, 27, 105020	1.8	2
155	Preparation of ideal molecular junctions: depositing non-invasive gold contacts on molecularly modified silicon. *Nanoscale*, **2011**, 3, 1434-45	7.7	22
154	Electrodeposition, characterization and morphological investigations of NiFe/Cu multilayers prepared by pulsed galvanostatic, dual bath technique. *Materials Characterization*, **2011**, 62, 204-210	3.9	12
153	Improved Performance of Nanohole Surface Plasmon Resonance Sensors by the Integrated Response Method. *IEEE Photonics Journal*, **2011**, 3, 441-449	1.8	22
152	Detecting Antibodies Secreted by Trapped Cells Using Extraordinary Optical Transmission. *IEEE Sensors Journal*, **2011**, 11, 2732-2739	4	7
151	Long-lasting flexible organic solar cells stored and tested entirely in air. *Applied Physics Letters*, **2011**, 99, 263305	3.4	9
150	Transport and strain relaxation in wurtzite InAs□GaAs core-shell heterowires. *Applied Physics Letters* , **2011**, 98, 152103	3.4	55
149	Rectifying characteristics of Te-doped GaAs nanowires. *Applied Physics Letters*, **2011**, 99, 182102	3.4	29
148	. *Journal of Medical and Biological Engineering*, **2011**, 31, 121	2.2	5
147	**2010**,		3
146	Effect of annealing on the structural and optical properties of heavily carbon-doped ZnO. *Semiconductor Science and Technology*, **2010**, 25, 045023	1.8	3
145	Misfit dislocations in nanowire heterostructures. *Semiconductor Science and Technology*, **2010**, 25, 024006	1.8	122
144	Resonant optical transmission through hole-arrays in metal films: physics and applications. *Laser and Photonics Reviews*, **2010**, 4, 311-335	8.3	124
143	A New Technique for Magnetic Nanoparticle Imaging Using Magnetoencephalography Frequency Data. *IFMBE Proceedings*, **2010**, 443-446	0.2	2
142	Residual Stress, Defects, and Electrical Properties of Epitaxial Copper Growth on GaAs. *Journal of the Electrochemical Society*, **2009**, 156, D138	3.9	11
141	Inhomogeneous magnetization processes in electrodeposited iron thin films on GaAs. *Journal of Applied Physics*, **2009**, 105, 07D543	2.5	2
140	Structural and Room-Temperature Transport Properties of Zinc Blende and Wurtzite InAs Nanowires. *Advanced Functional Materials*, **2009**, 19, 2102-2108	15.6	82

139	Growth of InAsSb/InAs MQWs on GaSb for mid-IR photodetector applications. *Journal of Crystal Growth*, **2009**, 311, 3563-3567	1.6	27
138	Atomic ordering in GaAsSb (0 0 1) grown by metalorganic vapor phase epitaxy. *Journal of Crystal Growth*, **2009**, 311, 4391-4397	1.6	5
137	Molecular orientation in octanedithiol and hexadecanethiol monolayers on GaAs and Au measured by infrared spectroscopic ellipsometry. *Langmuir*, **2009**, 25, 919-23	4	35
136	Field dependent transport properties in InAs nanowire field effect transistors. *Nano Letters*, **2008**, 8, 3114-9	11.5	30
135	Nanoscale Electrical and Structural Characterization of Gold/Alkyl Monolayer/Silicon Diode Junctions. *Journal of Physical Chemistry C*, **2008**, 112, 9081-9088	3.8	37
134	A new generation of sensors based on extraordinary optical transmission. *Accounts of Chemical Research*, **2008**, 41, 1049-57	24.3	423
133	Heteroepitaxial growth of vertical GaAs nanowires on Si(111) substrates by metal-organic chemical vapor deposition. *Nano Letters*, **2008**, 8, 3755-60	11.5	89
132	Plasmonic sensors based on nano-holes: technology and integration **2008**,		6
131	SU-8 polymer enclosed microchannels with interconnect and nanohole arrays as an optical detection device for biospecies. *Annual International Conference of the IEEE Engineering in Medicine and Biology Society IEEE Engineering in Medicine and Biology Society Annual International Conference*, **2008**, 2008, 5652-5	0.9	1
130	Epitaxial Fe[sub x]Ni[sub 1−x] Thin Film Contacts to GaAs via Electrochemistry. *Journal of the Electrochemical Society*, **2008**, 155, H841	3.9	8
129	Defect studies of ZnSe nanowires. *Nanotechnology*, **2008**, 19, 215715	3.4	30
128	Au–Ag and Au–Pd molecular contacts to GaAs. *Journal of Vacuum Science & Technology B*, **2008**, 26, 1597		6
127	Nanoholes in metals with applications to sensors and spectroscopy. *International Journal of Nanotechnology*, **2008**, 5, 1058	1.5	2
126	Structural and electrical characteristics of nanocrystalline silicon prepared by hot-wire chemical vapor deposition on polymer substrates. *Thin Solid Films*, **2008**, 516, 7418-7421	2.2	1
125	Structure and photoluminescence of ZnSe nanostructures fabricated by vapor phase growth. *Journal of Applied Physics*, **2007**, 101, 014326	2.5	33
124	Transparent conducting indium bismuth oxide. *Thin Solid Films*, **2007**, 515, 3760-3765	2.2	5
123	Apex-Enhanced Raman Spectroscopy Using Double-Hole Arrays in a Gold Film. *Journal of Physical Chemistry C*, **2007**, 111, 2347-2350	3.8	87
122	Twinning modulation in ZnSe nanowires. *Semiconductor Science and Technology*, **2007**, 22, 175-178	1.8	35

121	Structural and electrical characteristics of microcrystalline silicon prepared by hot-wire chemical vapor deposition using a graphite filament. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2007**, 25, 464-467	2.9	5
120	Structural Analysis of Nanocrystalline Silicon Prepared by Hot-wire Chemical Vapor Deposition on Polymer Substrates. *Materials Research Society Symposia Proceedings*, **2007**, 989, 3		1
119	Ballistic electron and photocurrent transport in Au-molecular layer-GaAs diodes. *Journal of Applied Physics*, **2007**, 102, 013703	2.5	11
118	Developing 1D nanostructure arrays for future nanophotonics. *Nanoscale Research Letters*, **2006**, 1, 99-119	3	42
117	Epitaxial Bi□GaAs diodes via electrodeposition. *Journal of Vacuum Science & Technology B*, **2006**, 24, 2138		17
116	Effects of HWCVD-deposited Seed Layers on Hydrogenated Microcrystalline Silicon Films on Glass Substrates. *Materials Research Society Symposia Proceedings*, **2006**, 910, 5		1
115	Epitaxial Bi□GaAs(111) diodes via electrodeposition. *Applied Physics Letters*, **2006**, 88, 022102	3.4	17
114	Enhancement of band edge luminescence in ZnSe nanowires. *Journal of Applied Physics*, **2006**, 100, 084316	2.5	67
113	Surface plasmon-quantum dot coupling from arrays of nanoholes. *Journal of Physical Chemistry B*, **2006**, 110, 8307-13	3.4	56
112	Microstructure of ordered nanodomains induced by Bi surfactant in OMVPE-grown GaAsSb. *Journal of Crystal Growth*, **2006**, 287, 541-544	1.6	3
111	Aligned Co nanodiscs by electrodeposition on GaAs. *Journal of Crystal Growth*, **2006**, 287, 514-517	1.6	20
110	Planar defects and phase transformation in ZnSe nanosaws. *Journal of Materials Science: Materials in Electronics*, **2006**, 17, 1065-1070	2.1	9
109	Structural and magnetic properties of NiMnSb/InGaAs/InP(001). *Journal of Applied Physics*, **2005**, 97, 073906	2.5	15
108	Ballistic electron emission microscopy studies of Au/molecule/n-GaAs diodes. *Journal of Physical Chemistry B*, **2005**, 109, 6252-6	3.4	31
107	Basis and lattice polarization mechanisms for light transmission through nanohole arrays in a metal film. *Nano Letters*, **2005**, 5, 1243-6	11.5	63
106	Enhanced fluorescence from arrays of nanoholes in a gold film. *Journal of the American Chemical Society*, **2005**, 127, 14936-41	16.4	179
105	Strain relaxation by <100> misfit dislocations in dilute nitride InxGa1□As1□yNy/GaAs quantum wells. *Physica Status Solidi (A) Applications and Materials Science*, **2005**, 202, 2849-2857	1.6	7
104	Temporary extrusion failures in accelerated lifetime tests of copper interconnects. *IEEE Electron Device Letters*, **2005**, 26, 622-624	4.4	2

103	Characterization of Temporary Extrusion Failures in Quarter-Micron Copper Interconnects. *Materials Research Society Symposia Proceedings*, **2005**, 863, B9.7-1		
102	Electrokinetically-Induced Flow Over a Nano-Hole Array Sensor **2004**, 213		0
101	Effects of capillary forces on copper–dielectric interfacial void evolution. *Applied Physics Letters*, **2004**, 84, 5201-5203	3.4	8
100	Effect of Bi surfactant on atomic ordering of GaAsSb. *Applied Physics Letters*, **2004**, 85, 5589-5591	3.4	10
99	Strong polarization in the optical transmission through elliptical nanohole arrays. *Physical Review Letters*, **2004**, 92, 037401	7.4	384
98	Evolution of interface voids under current and temperature stress in integrated circuit metallization. *Metals and Materials International*, **2004**, 10, 411-415	2.4	4
97	Surface plasmon sensor based on the enhanced light transmission through arrays of nanoholes in gold films. *Langmuir*, **2004**, 20, 4813-5	4	620
96	Nanohole-Enhanced Raman Scattering. *Nano Letters*, **2004**, 4, 2015-2018	11.5	382
95	Antimony segregation in GaAs-based multiple quantum well structures. *Journal of Crystal Growth*, **2003**, 254, 28-34	1.6	22
94	Substrate effects on the ferroelectric properties of fine-grained BaTiO3 films. *Journal of Applied Physics*, **2003**, 94, 5982-5989	2.5	25
93	Growth, branching, and kinking of molecular-beam epitaxial <110> GaAs nanowires. *Applied Physics Letters*, **2003**, 83, 3368-3370	3.4	102
92	Evolution of GaSb/GaAs Quantum Dot Strain Relaxation. *Microscopy and Microanalysis*, **2002**, 8, 1200-1201	1.5	
91	Comparison of strain relaxation in InGaAsN and InGaAs thin films. *Applied Physics Letters*, **2002**, 80, 4357-4359	3.4	20
90	Scanning spreading resistance microscopy current transport studies on doped III–V semiconductors. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2002**, 20, 1682		33
89	Wavelength-Invariant Resist Composed of Bimetallic Layers. *Materials Research Society Symposia Proceedings*, **2002**, 745, 381		1
88	Ballistic electron emission microscopy studies of ZnSe–BeTe heterojunctions. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2002**, 20, 1781		
87	The growth of SiGe on sapphire using rapid thermal chemical vapor deposition. *Journal of Crystal Growth*, **2001**, 222, 20-28	1.6	9
86	X-Ray Diffuse Scattering from Misfit Dislocation at Buried Interface. *Materials Research Society Symposia Proceedings*, **2001**, 673, 1		4

85	Faceting transition in epitaxial growth of dilute GaNAs films on GaAs. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2001**, 19, 1417		11
84	Calibrated scanning spreading resistance microscopy profiling of carriers in III□V structures. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2001**, 19, 1662		29
83	Anisotropic resistivity correlated with atomic ordering in p-type GaAsSb. *Applied Physics Letters*, **2001**, 79, 2384-2386	3.4	27
82	Gas-source molecular beam epitaxial growth and thermal annealing of GaInNAs/GaAs quantum wells. *Journal of Crystal Growth*, **2000**, 208, 145-152	1.6	33
81	Interfacial scattering of hot electrons in ultrathin Au/Co films. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2000**, 18, 2047		5
80	Hot-electron attenuation lengths in ultrathin magnetic films. *Journal of Applied Physics*, **2000**, 87, 5164-5166	2.5	20
79	Atomic interface structure-property investigations. *Canadian Journal of Physics*, **2000**, 77, 985-994	1.1	
78	Atomic interface structure-property investigations. *Canadian Journal of Physics*, **2000**, 78, 201-210	1.1	0
77	Quantum dot-like behavior of GaInNAs in GaInNAs/GaAs quantum wells grown by gas-source molecular-beam epitaxy. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1999**, 17, 1649		18
76	Suppression of growth-induced perpendicular magnetic anisotropy in Co□Pt alloys by trace amounts of Si. *Applied Physics Letters*, **1999**, 75, 4177-4179	3.4	1
75	Observation of quantum dot-like behavior of GaInNAs in GaInNAs/GaAs quantum wells. *Applied Physics Letters*, **1999**, 74, 2337-2339	3.4	120
74	Effects of rapid thermal annealing on GaInNAs/GaAs multiple quantum wells. *Journal of Crystal Growth*, **1999**, 201-202, 419-422	1.6	61
73	Growth-induced magnetic anisotropy and clustering in vapor-deposited Co-Pt alloy films. *Physical Review B*, **1999**, 60, 12826-12836	3.3	49
72	Hole confinement and low-frequency noise in SiGe pFETs on silicon-on-sapphire. *IEEE Electron Device Letters*, **1999**, 20, 173-175	4.4	8
71	Effects of GaAs substrate misorientation on strain relaxation in InxGa1□As films and multilayers. *Journal of Applied Physics*, **1998**, 83, 5137-5149	2.5	91
70	Effect of Oxygen on the Degradation of Ti-Si-N Diffusion Barriers in Cu Metallization. *Materials Research Society Symposia Proceedings*, **1998**, 514, 321		1
69	Analysis of Sige Fet Device Structures on Silicon-on-sapphire Substrates by X-Ray Diffraction. *Materials Research Society Symposia Proceedings*, **1998**, 533, 55		1
68	In-situ measurement of roughness spectra using diffuse scattering **1997**,		1

67	Compositional Effects on the Degradation of PVD-TiSiN. *Materials Research Society Symposia Proceedings*, **1997**, 472, 325		1
66	Compositional Effects on the Degradation of PVD-Tisin. *Materials Research Society Symposia Proceedings*, **1997**, 473, 241		
65	Role of interface microstructure in rectifying metal/semiconductor contacts: Ballistic electron emission observations correlated to microstructure. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1996**, 14, 1238		14
64	Tensile strain relaxation in GaNxP1 (x 0.1) grown by chemical beam epitaxy. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1996**, 14, 2952		11
63	Modulation-doped In0.53Ga0.47As/In0.52Al0.48As heterostructures grown on GaAs substrates using step-graded InxGa1 As buffers. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1996**, 14, 3035		7
62	Au/ZnSe contacts characterized by ballistic electron emission microscopy. *Journal of Applied Physics* , **1996**, 79, 1532-1535	2.5	14
61	A Study of Low-Temperature Grown GaP by Gas-Source Molecular Beam Epitaxy. *Materials Research Society Symposia Proceedings*, **1996**, 421, 293		
60	Correlation of buffer strain relaxation modes with transport properties of two-dimensional electron gases. *Journal of Applied Physics*, **1996**, 80, 6849-6854	2.5	9
59	Comparison of Au contacts to Si, GaAs, InxGa1 xP, and ZnSe measured by ballistic electron emission microscopy. *Materials Chemistry and Physics*, **1996**, 46, 224-229	4.4	8
58	Relationship between surface morphology and strain relaxation during growth of InGaAs strained layers. *Applied Physics Letters*, **1995**, 67, 3744-3746	3.4	32
57	Study of h-scale spatial variations in strain of a compositionally step-graded InxGa1 As/GaAs(001) heterostructure. *Applied Physics Letters*, **1995**, 66, 869-871	3.4	25
56	Relaxation-induced polarized luminescence from InxGa1-xAs films grown on GaAs(001). *Physical Review B*, **1995**, 51, 5033-5037	3.3	12
55	Influence of GaAs(001) substrate misorientation towards {111} on the optical properties of InxGa1 As/GaAs. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1995**, 13, 1766		2
54	Correlation of anisotropic strain relaxation with substrate misorientation direction at InGaAs/GaAs(001) interfaces. *Applied Physics Letters*, **1995**, 67, 344-346	3.4	30
53	Effects of Substrate Misorientation Direction on Strain Relaxation at InGaAs/GaAs(001) Interfaces. *Materials Research Society Symposia Proceedings*, **1995**, 379, 21		
52	Beem and UHV-Tem Studies of PtSi/Si(001). *Materials Research Society Symposia Proceedings*, **1995**, 402, 461		2
51	Structural and Electrical Characterization of Si-Implanted TiN as a Diffusion Barrier for Cu Metallization. *Materials Research Society Symposia Proceedings*, **1995**, 391, 327		
50	Room-temperature electrosynthesis of carbonaceous fibers. *Advanced Materials*, **1995**, 7, 398-401	24	7

49	Homogeneous Strain Relaxation and Mosaic Spread in IngaAs/GaAs Heterostructures Using Triple Axis Diffractometry **1995**, 221-226		1
48	Homogeneous Strain Relaxation and Mosaic Spread in InGaAs/GaAs Heterostructures Using Triple Axis Diffractometry. *Advances in X-ray Analysis*, **1994**, 38, 221-226		
47	Nanometer-resolved spatial variations in the Schottky barrier height of a Au/n-type GaAs diode. *Physical Review B*, **1994**, 49, 16474-16479	3.3	43
46	Strain relaxation induced deep levels in In1−xGaxAs thin films. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1994**, 12, 1050-1053	2.9	2
45	Optical detection of misfit dislocation-induced deep levels at InGaAs/GaAs heterojunctions. *Applied Physics Letters*, **1994**, 64, 3572-3574	3.4	12
44	Lateral variation in the Schottky barrier height of Au/PtSi/(100)Si diodes. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1994**, 12, 2634		25
43	Dislocation-Induced deep level states in In0.08Ga0.92As/GaAs heterostructures. *Journal of Electronic Materials*, **1994**, 23, 929-933	1.9	3
42	Anisotropic structural, electronic, and optical properties of InGaAs grown by molecular beam epitaxy on misoriented substrates. *Applied Physics Letters*, **1994**, 65, 1424-1426	3.4	19
41	Lateral Variation in the Schottky Barrier Height and Observation of Critical Lengths at Au/PtSi/(100)Si and Au/(100)GaAs Diodes. *Materials Research Society Symposia Proceedings*, **1994**, 337, 319		2
40	Anisotropic Structural and Electronic Properties of InGaAs/GaAs Heterojunctions. *Materials Research Society Symposia Proceedings*, **1994**, 340, 349		1
39	The Effect of Starting Silicon Crystal Structure on Photoluminescence Intensity of Porous Silicon. *Materials Research Society Symposia Proceedings*, **1994**, 358, 351		1
38	Light Scattering Study of the Evolution of the Surface Morphology During Growth of Ingaas on GaAs. *Materials Research Society Symposia Proceedings*, **1994**, 375, 193		
37	Control of surface morphology and strain relaxation in InGaAs grown on GaAs using a step-graded buffer **1994**, 2140, 179		3
36	Si diffusion and segregation in low-temperature grown GaAs. *Applied Physics Letters*, **1993**, 62, 286-288	3.4	8
35	Time dependent ballistic electron emission microscopy studies of a Au/(100)GaAs interface with a native oxide diffusion barrier. *Applied Physics Letters*, **1993**, 62, 2965-2967	3.4	24
34	Multiple dislocation loops in linearly graded InxGa1−xAs (0≤x≤0.53) on GaAs and InxGa1−xP (0≤x≤0.32) on GaP. *Applied Physics Letters*, **1993**, 63, 500-502	3.4	24
33	Gas-source molecular beam epitaxial growth, characterization, and light-emitting diode application of InxGa1−xP on GaP(100). *Applied Physics Letters*, **1993**, 62, 2369-2371	3.4	25
32	Anisotropic Surface Roughness in Strain Relaxed in0.40GA0.60on Gaas with a Step-Graded INXGA1-XAs Buffer Layer. *Materials Research Society Symposia Proceedings*, **1993**, 312, 107		4

31	Modulation-doped In0.3Ga0.7As/In0.29Al0.71As heterostructures grown on GaAs by step grading. *Semiconductor Science and Technology*, **1992**, 7, 601-603	1.8	16
30	Oxidation induced AlAs/GaAs superlattice disordering. *Applied Physics Letters*, **1992**, 60, 1235-1237	3.4	1
29	Lattice tilt and dislocations in compositionally step-graded buffer layers for mismatched InGaAs/GaAs heterointerfaces. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1992**, 10, 1820		46
28	Lattice strain from substitutional Ga and from holes in heavily doped Si:Ga. *Physical Review B*, **1992**, 45, 3323-3331	3.3	19
27	Growth and Characterization of InxGa1s-xP(x□0.38) on GaP(1OO) with a Linearly Graded Buffer Layer by Gas-Source Molecular Beam Epitaxy. *Materials Research Society Symposia Proceedings*, **1992**, 281, 227		
26	Beem Investigation of Oxide and Sulfide Passivated GaAs. *Materials Research Society Symposia Proceedings*, **1992**, 281, 653		3
25	Strain relaxation of compositionally graded InxGa1□As buffer layers for modulation-doped In0.3Ga0.7As/In0.29Al0.71As heterostructures. *Applied Physics Letters*, **1992**, 60, 1129-1131	3.4	83
24	Luminescent colloidal silicon suspensions from porous silicon. *Science*, **1992**, 255, 66-8	33.3	206
23	Oxidation and Diffusion at Poly-SiGe/GaAs Interfaces. *Materials Research Society Symposia Proceedings*, **1991**, 240, 581		
22	Luminescent Colloidal SI Suspensions from Porous SI. *Materials Research Society Symposia Proceedings*, **1991**, 256, 131		1
21	High-resolution x-ray diffraction of InAlAs/InP superlattices grown by gas source molecular beam epitaxy. *Applied Physics Letters*, **1991**, 58, 1530-1532	3.4	16
20	Preparation of Cross Sectional TEM Samples Using Lithographic Techniques and Reactive Ion Etching. *Materials Research Society Symposia Proceedings*, **1990**, 199, 43		1
19	Planar Ge/Pd and alloyed Au-Ge-Ni ohmic contacts to n-AlxGa1□As (0□0.3). *Applied Physics Letters*, **1989**, 54, 721-723	3.4	17
18	Lattice Strain from Holes in Heavily Doped Si:Ga. *Materials Research Society Symposia Proceedings*, **1989**, 147, 53		
17	Asymmetries in dislocation densities, surface morphology, and strain of GaInAs/GaAs single heterolayers. *Journal of Applied Physics*, **1988**, 64, 4843-4852	2.5	195
16	Lattice compression from conduction electrons in heavily doped Si:As. *Physical Review Letters*, **1988**, 61, 1748-1751	7.4	102
15	The interdiffusion of Si, P, and In at polysilicon/GaAs interfaces. *Journal of Applied Physics*, **1988**, 64, 1845-1854	2.5	36
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13	Vacancy Diffusion at Polysilicon Encapsulated GaAs Surfaces. *Materials Research Society Symposia Proceedings*, **1987**, 104, 463		
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